IN THE SPECIFICATION

Please replace the paragraph at page 9, lines 15-19, with the following rewritten paragraph:

In particular, when a monocrystalline silicon thin film is used as a photovoltaic layer of solar cells, even when a very small amount of metal elements, such as 0.1 ppm or less, is contained, the energy conversion efficiency of a solar cell is seriously degraded ~~(see Fig. 3)~~.

Please delete the paragraph beginning at page 9, line 20 to page 10, line 1:

~~Fig. 3 includes graphs showing the influence of various elements at various concentrations contained in a monocrystalline silicon thin film on the power generation efficiency of a solar cell, the influence being a conventional problem. Fig. 3(a) is a graph showing the influence on n-type silicon, and Fig. 3(b) is a graph showing the influence on p-type silicon.~~

Please delete the paragraph beginning at page 20, line 24 to page 21, line 4:

~~Fig. 3 includes graphs showing the influence of various elements at various concentrations contained in a monocrystalline silicon thin film on the power generation efficiency of a solar cell, the influence being a conventional problem.~~

Please replace the paragraph beginning at page 46, line 21 to page 47, line 13, with the following rewritten paragraph:

Features of a RVD method will be described in detail with reference to a highly doped sacrificial layer formed by using B or P. Since a targeted thickness of a monocrystalline silicon thin film is 10 μm, the thickness of the sacrificial layer is preferably one tenth thereof or less, that is, 1 μm or less. When a dopant (B, P) diffuses 1 μm, the structure of the

sacrificial layer is degraded, and when the diffusion coefficient is represented by D, the time constant in this case is (1 μm)$^2$/D. Since the monocrystalline silicon thin film located at the upper side must be grown to have a thickness of 10 μm or more within this period, the film growth rate GR must be more than 10D/1 μm. By using a known relationship between a diffusion coefficient D and a temperature T, the following equation, GR > 2x10$^{12}$exp (-325 [kJ/mol]/8.31[J/mol·K] / (T+273) [K]), is obtained. Fig. 17 is a graph showing the relationship between the temperature and the film growth rate thus obtained. <u>The source of Fig. 17 is: P.A. Coon, M.L. Wise, S.M. George. J. Cryst. Growth 130, 162 (1933).</u>